

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 4, line 23, with the following rewritten paragraph:

-- Referring to Figure 1, there is a cross-section representing an example of a semiconductor device according to Implementation mode 1 of the present invention. Figure 2 is a perspective view showing one mode of the semiconductor element represented in Figure 1. In a semiconductor device 100 of Figure 1, there is a semiconductor element 1 having a main surface 1a. There is a substrate 2 which is integrated with a frame part 2c on which the element is mounted. Substrate 2 has an upper surface 2a and a lower surface 2b. There is a distance H between these two surfaces. Main surface 1a of semiconductor element 1 is opposite upper surface 2a of substrate 2. In the present situation, main surface 1a is a rectangle. The length of the long side of main surface 1a is a length L, corresponds to that of long side 11. The length in the short side direction corresponds to that of short side 12. This is the same for other implementation modes, but if main surface 1a is rectangular, normally, the surface of the other side is approximately the same shape. However, this does not always have to be the case. As shown in Figure 3, there are examples of the main surface being other than a rectangle. The length in the long direction of the main surface of the semiconductor element of the present invention is measured from the outline of an image projected in a direction perpendicular to the main surface. Examples are shown in Figures 3A through 3E. The part displayed as L is the length in the long direction. For example, if it is a circle or square, length L is the diameter or the length of one of its sides, respectively. If it is an ellipse, it is the length of the major axis. The distance between the upper surface and the lower surface of the substrate is H. In the semiconductor device of the present invention, ratio L/H H/L is 0.3 or greater. Preferably ratio L/H H/L is 0.45 to 1.5, and more preferably it is between 0.5 and 1.25. --

Please also replace the paragraph beginning on page 16, line 23, with the following rewritten paragraph:

-- The semiconductor light emitting elements 1 from Samples 1 through 10 were illuminated with a current of 1A. After one minute of illumination, temperatures T1 were measured

by using a radiation thermometer (non-contact). Illumination was continued, and after three minutes of illumination, measurements for temperature T3 were taken for each of Samples 1 through ~~9~~ 10. --